MMBT5401L, SMMBT5401L, NSVMMBT5401L

High Voltage Transistor PNP Silicon

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-150	Vdc
Collector – Base Voltage	V _{CBO}	-160	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-500	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$ Derate Above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate Above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

1. FR-5 = 1.0 \times 0.75 \times 0.062 in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in 99.5% alumina.

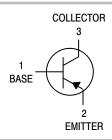


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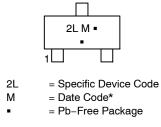
http://onsemi.com



SOT-23 (TO-236) CASE 318 STYLE 6



MARKING DIAGRAM



(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]					
MMBT5401LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel					
SMMBT5401LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel					
MMBT5401LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel					
NSVMMBT5401LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel					

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
DFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage $(I_{C} = -1.0 \text{ mAdc}, I_{B} = 0)$	V _{(BR)CEO}	-150	_	Vdc
Collector – Base Breakdown Voltage $(I_{C} = -100 \ \mu Adc, I_{E} = 0)$	V _(BR) CBO	-160	-	Vdc
Emitter – Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0	-	Vdc
Collector-Base Cutoff Current ($V_{CB} = -120$ Vdc, $I_E = 0$) ($V_{CB} = -120$ Vdc, $I_E = 0$, $T_A = 100^{\circ}C$)	Ісво	-	-50 -50	nAdc μAdc

ON CHARACTERISTICS

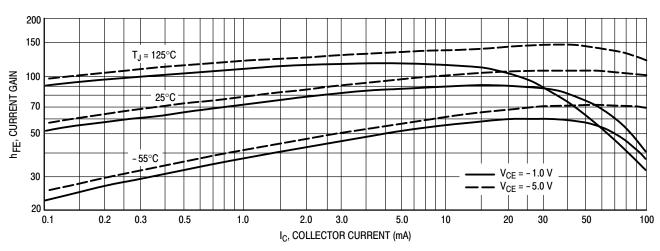
	h _{FE}	50 60 50	_ 240 _	-
Collector – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}$, $I_B = -1.0 \text{ mAdc}$) ($I_C = -50 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$)	V _{CE(sat)}	-	-0.2 -0.5	Vdc
Base – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$) ($I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)	V _{BE(sat)}	-	-1.0 -1.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

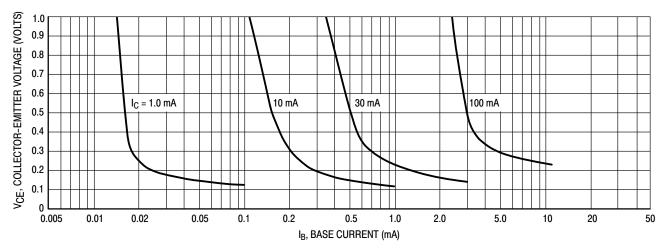
Current – Gain — Bandwidth Product	f _T			MHz
(I _C = -10 mAdc, V _{CE} = -10 Vdc, f = 100 MHz)		100	300	
Output Capacitance	C _{obo}			pF
(V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)		-	6.0	
Small Signal Current Gain	h _{fe}			-
(I _C = –1.0 mAdc, V _{CE} = –10 Vdc, f = 1.0 kHz)		40	200	
Noise Figure	NF			dB
(I_C = -200 μ Adc, V _{CE} = -5.0 Vdc, R _S = 10 Ω , f = 1.0 kHz)		-	8.0	

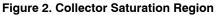
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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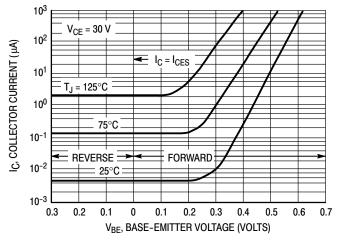
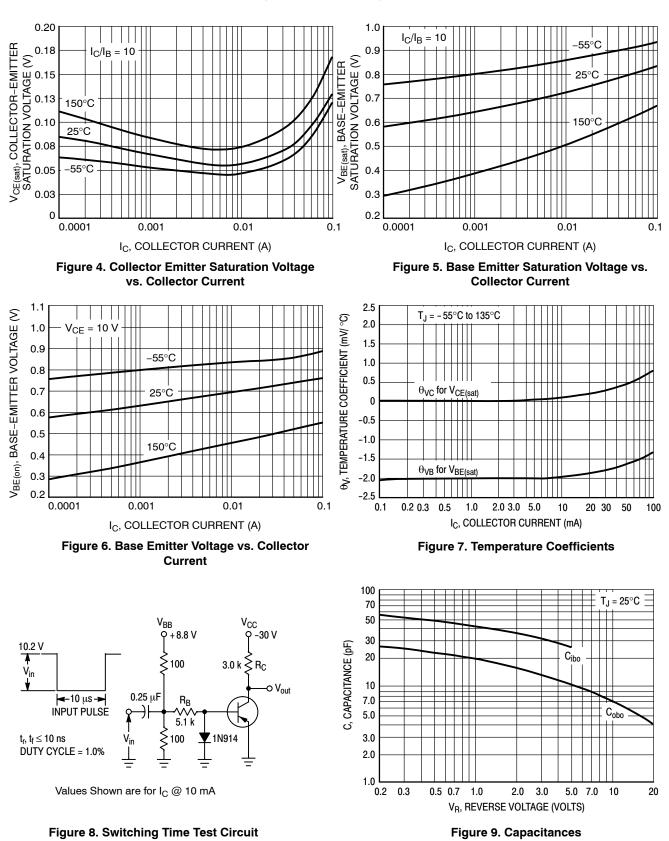
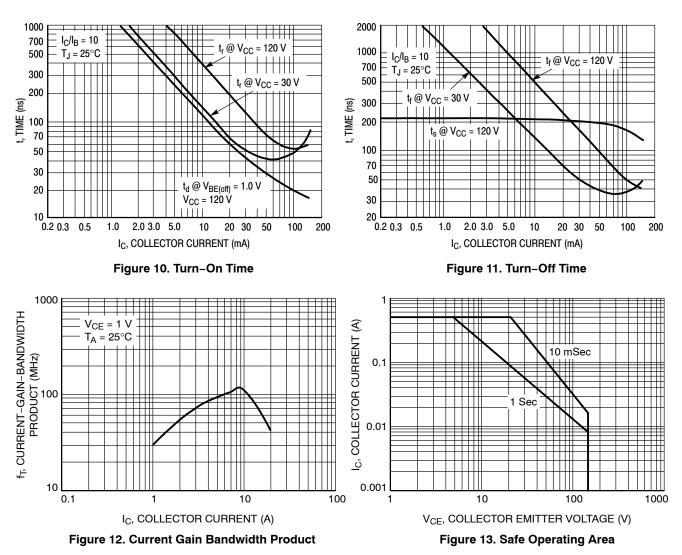


Figure 3. Collector Cut-Off Region

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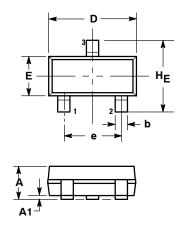


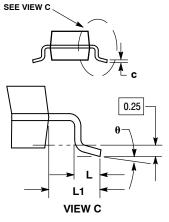


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PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AP





NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 - MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

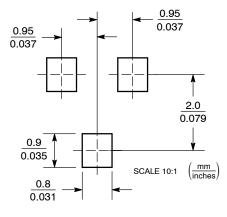
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6:

PIN 1. BASE 2. EMITTEI

2. EMITTER
 3. COLLECTOR

SOLDERING FOOTPRINT



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